

- ✎ L23: (14) 30 and 32
- ✎ L21: (6) 15 and 27
- ✎ L29: (11) 19 and 27
- ✎ L34: (0) budget
- ✎ L35: (16972) budget
- ✎ L36: (1818490) insulat\$4 dielectric
- ✎ L37: (3946048) budget require\$4
- ✎ L38: (117663) 22 near\$ 37
- ✎ L39: (5522) 36 with 88
- ✎ L40: (3862) 35 near\$ 22
- ✎ L41: (428140 with 36
- ✎ L42: (0) 41 and 19
- ✎ L43: (1) 39 and 19
- ✎ L44: (282) 41 and 5
- ✎ L45: (227) 44 and 9
- ✎ L46: (345089) "450"
- ✎ L47: (48) 44 and 46
- ✎ L48: (10) 41 with 46
- ✎ L19: (50) 10 15 17
- ✎ Failed
- ✎ Saved
- ✎ S4: (0) 10/815470
- ✎ S5: (361489) grain
- ✎ S6: (148802) crystal\$9 near2 (orient\$6 grow\$4 (face\$2 facing state))
- ✎ S7: (2573) electron adj scatter\$4
- ✎ S8: (2589552) interconnect\$2 plus 40

10 15 17

May 2005

	U	I	Inventor	Document	Issue P	Title	Current	Current K	Retrieval	S	C	P	Q	Image	Doc P
1	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Hirao, Shuji	US 2004007	2004	15 Production method of semiconductor	438/85	438/643		<input type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>		US 2004007
2	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Ong, Edith	US 2004010	2004	15 Method for recrystallizing metal in feat	257/75			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>		US 2004010
3	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Seo, Soon-	US 2004000	2004	9 Method of forming planar Cu Interconn	216/83	257/E21.9		<input type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>		US 2004000
4	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Kaloyeros; U6	607571	2008	2 Conformal pure and doped aluminum e	427/57	257/E21.17		<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>		US 607571
5	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Inoue, Yasu	US 589526	1999	17 Semiconductor device having gap-met	438/84	257/E23.1		<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>		US 589526
6	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Hortikoshi, U	2004018	2004	2 Method for manufacturing a magnetic	438/62			<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>		US 2004018
7	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Ohno, Taka	US 2004002	2004117	Re-writable optical recording medium	430/27	369/275.2		<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>		US 2004002
8	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Hobukuni, N	US 2004002	2004177	Re-writable optical recording medium,	369/47			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>		US 2004002
9	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Hobukuni, N	US 2004018	2004	75 Re-writable optical recording medium,	369/47			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>		US 2004018
10	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Shimada, N	US 2004018	2004	8 Wiring structure for semiconductor de	257/76			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>		US 2004018